

STARPOWER**SEMICONDUCTOR****IGBT****GD100HFU120C8S****1200V/100A 2 in one-package**

Features

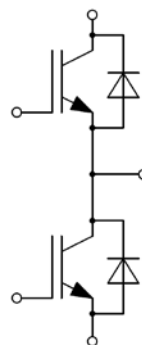
- NPT IGBT technology
- 10 μ s short circuit capability
- Low switching losses
- Rugged with ultrafast performance
- $V_{CE(sat)}$ with positive temperature coefficient
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Typical Applications

- Switching mode power supply
- Inductive heating
- Electronic welder

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	154	A
	@ $T_C=80^{\circ}\text{C}$	100	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	200	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	791	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	100	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	200	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	150	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +125	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	4000	V

IGBT Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=100\text{A}, V_{GE}=15\text{V}, T_j=25^{\circ}\text{C}$		2.90	3.35	V
		$I_C=100\text{A}, V_{GE}=15\text{V}, T_j=125^{\circ}\text{C}$		3.60		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=2.0\text{mA}, V_{CE}=V_{GE}, T_j=25^{\circ}\text{C}$	4.5	5.5	6.5	V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$			5.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^{\circ}\text{C}$			400	nA
R_{Gint}	Internal Gate Resistance			1.25		Ω
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		6.52		nF
C_{res}	Reverse Transfer Capacitance			0.41		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		1.12		μC
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=100\text{A}, R_G=9.1\Omega, V_{GE}=\pm 15\text{V}, T_j=25^{\circ}\text{C}$		265		ns
t_r	Rise Time			66		ns
$t_{d(off)}$	Turn-Off Delay Time			357		ns
t_f	Fall Time			124		ns
E_{on}	Turn-On Switching Loss			4.15		mJ
E_{off}	Turn-Off Switching Loss			3.10		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=100\text{A}, R_G=9.1\Omega, V_{GE}=\pm 15\text{V}, T_j=125^{\circ}\text{C}$		270		ns
t_r	Rise Time			67		ns
$t_{d(off)}$	Turn-Off Delay Time			368		ns
t_f	Fall Time			155		ns
E_{on}	Turn-On Switching Loss			5.86		mJ
E_{off}	Turn-Off Switching Loss			4.45		mJ
I_{SC}	SC Data	$t_P \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=125^{\circ}\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		800		A

Diode Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$		1.95	2.40	V
		$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=125^{\circ}\text{C}$		2.00		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=100\text{A},$ $-di/dt=1550\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^{\circ}\text{C}$		6.83		μC
I_{RM}	Peak Reverse Recovery Current			88.3		A
E_{rec}	Reverse Recovery Energy			2.62		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=100\text{A},$ $-di/dt=1550\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^{\circ}\text{C}$		12.7		μC
I_{RM}	Peak Reverse Recovery Current			134		A
E_{rec}	Reverse Recovery Energy			5.09		mJ

Module Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance			26	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.62		m Ω
R_{thJC}	Junction-to-Case (per IGBT)			0.158	K/W
	Junction-to-Case (per Diode)			0.271	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.146		K/W
	Case-to-Heatsink (per Diode)		0.250		
	Case-to-Heatsink (per Module)		0.046		
M	Terminal Connection Torque, Screw M5	2.5		5.0	N.m
	Mounting Torque, Screw M6	3.0		5.0	
G	Weight of Module		200		g

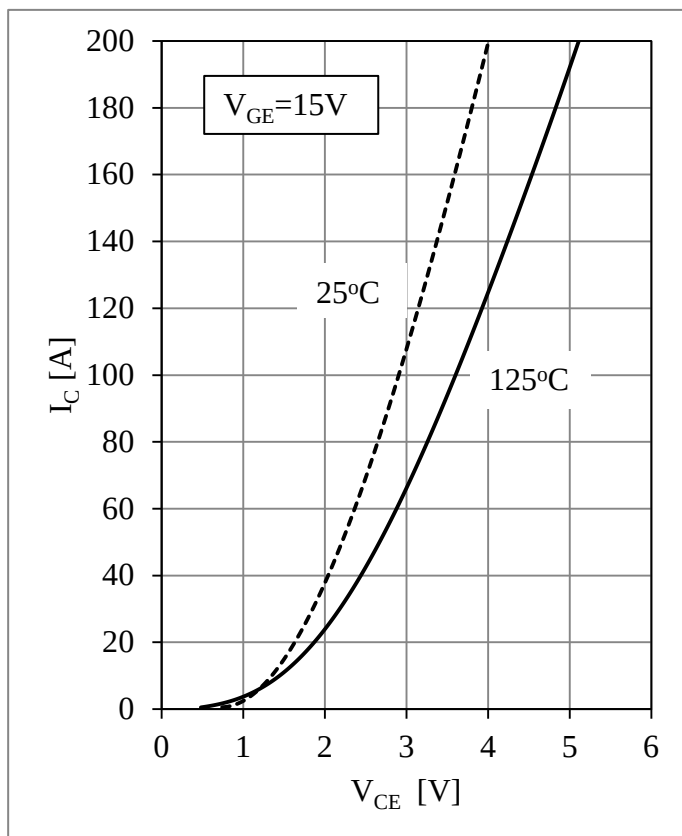


Fig 1. IGBT Output Characteristics

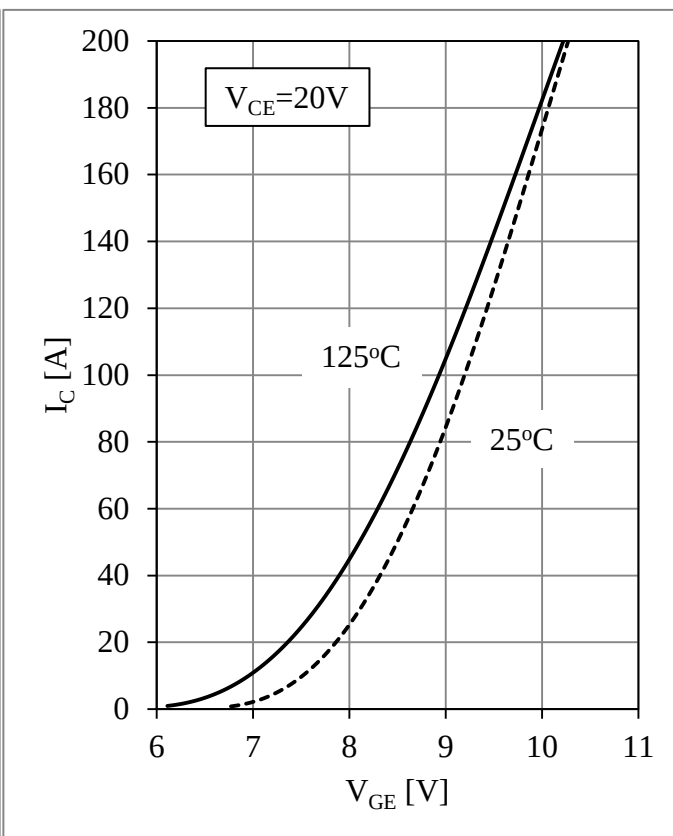
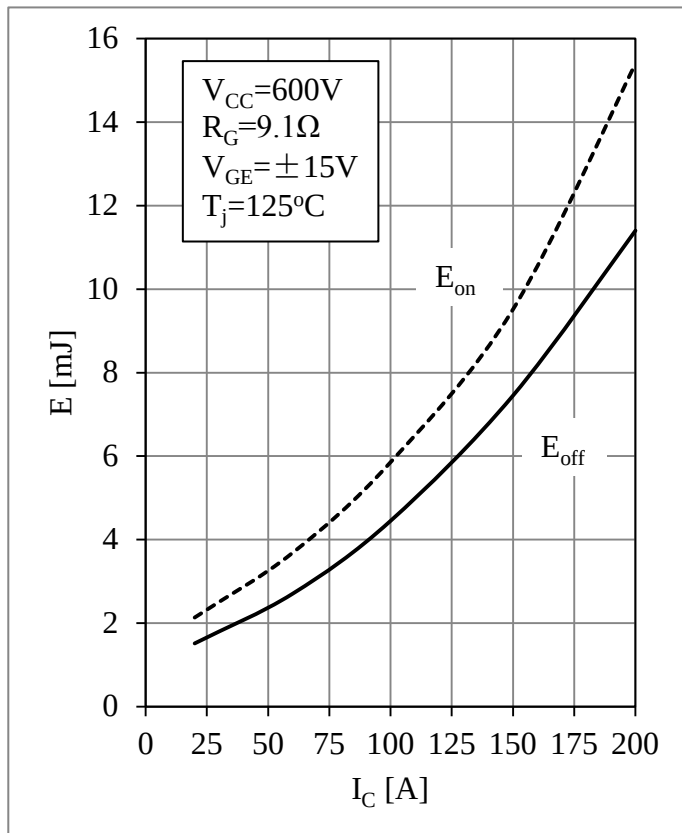
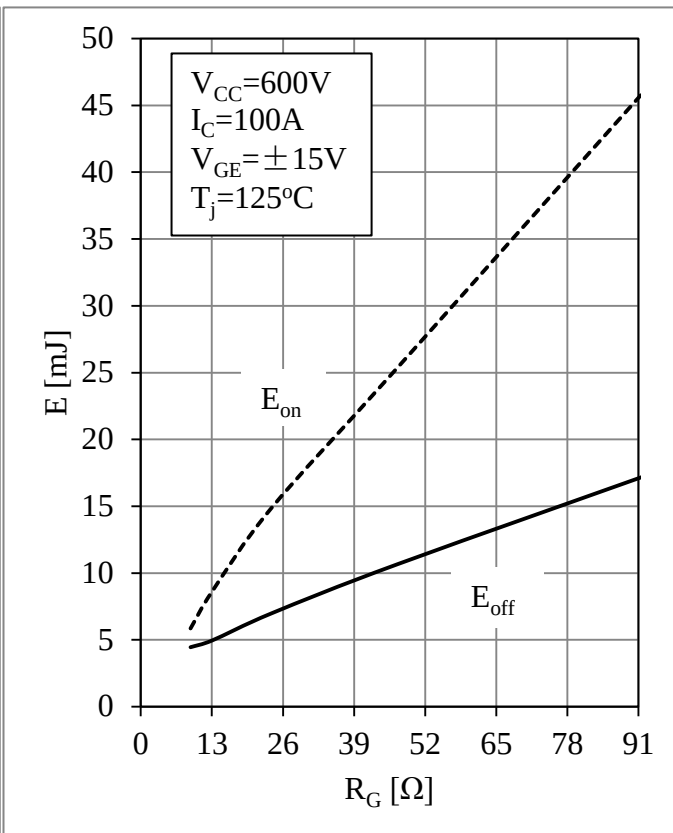


Fig 2. IGBT Transfer Characteristics

Fig 3. IGBT Switching Loss vs. I_C Fig 4. IGBT Switching Loss vs. R_G

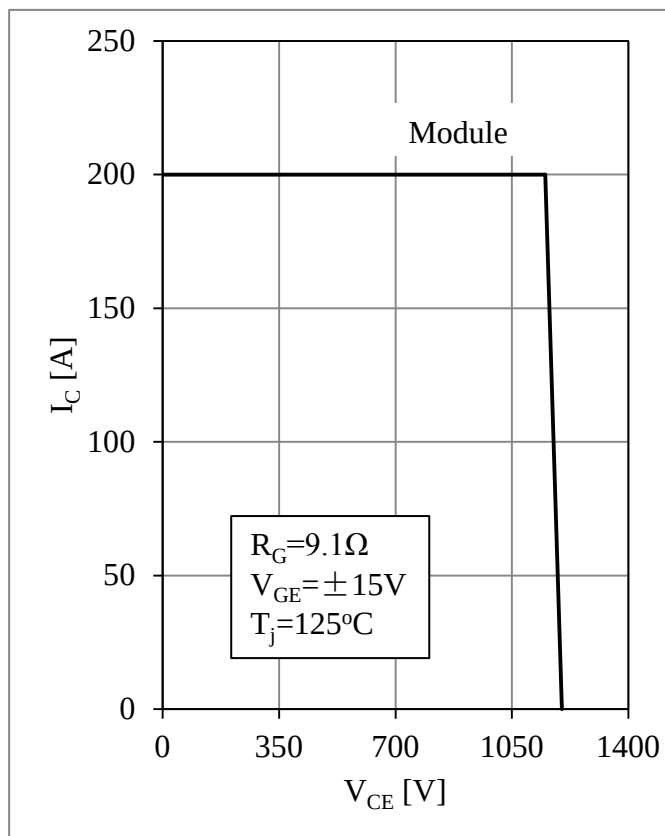


Fig 5. RBSOA

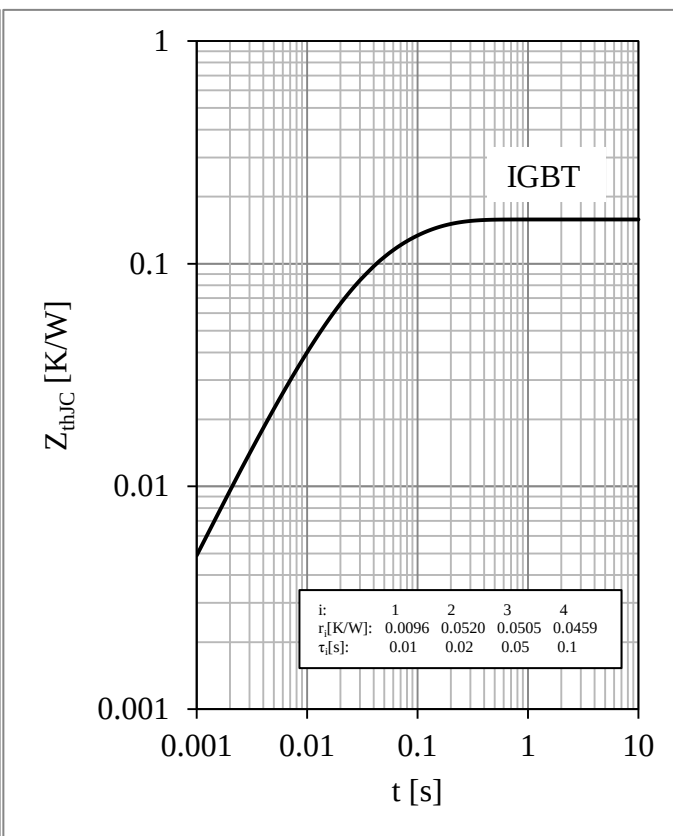


Fig 6. IGBT Transient Thermal Impedance

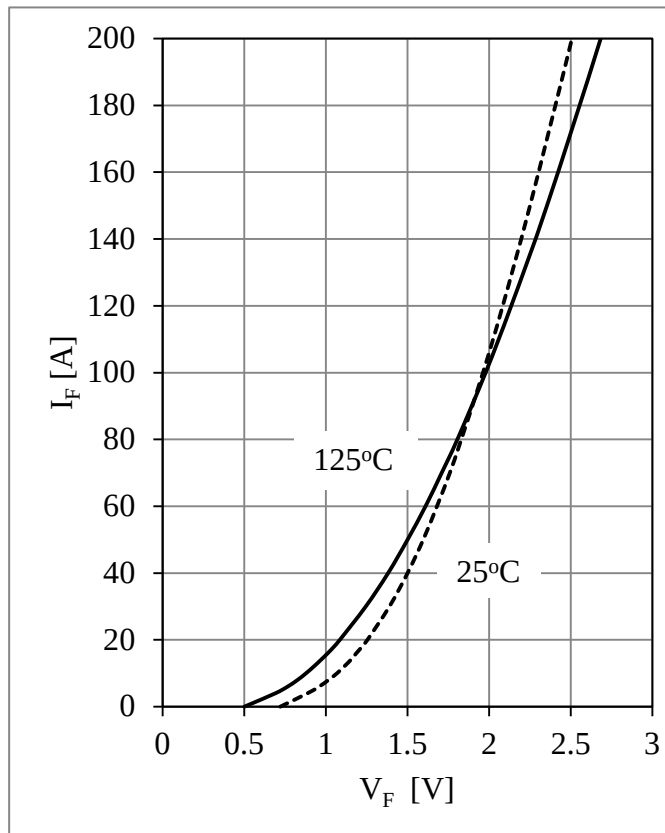
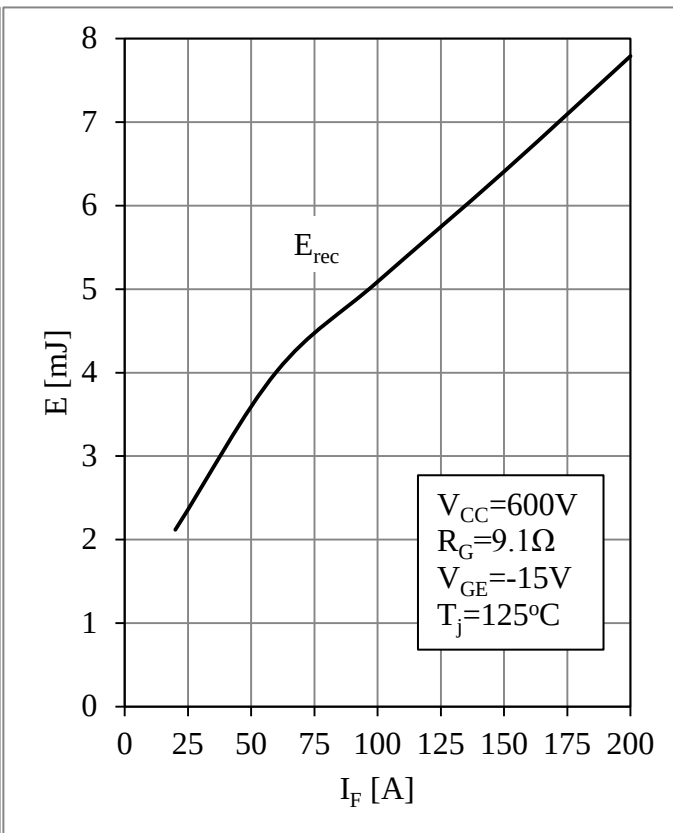


Fig 7. Diode Forward Characteristics

Fig 8. Diode Switching Loss vs. I_F

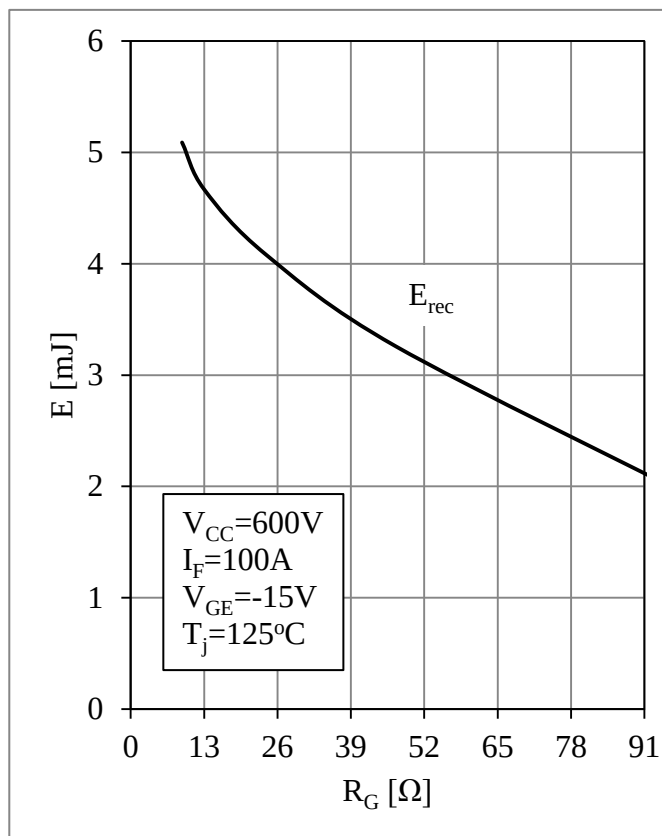
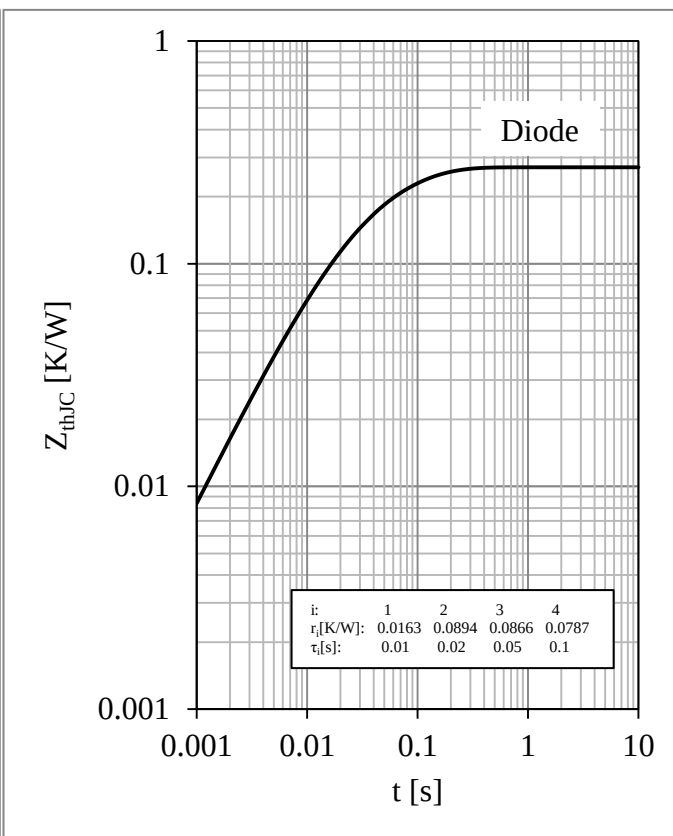
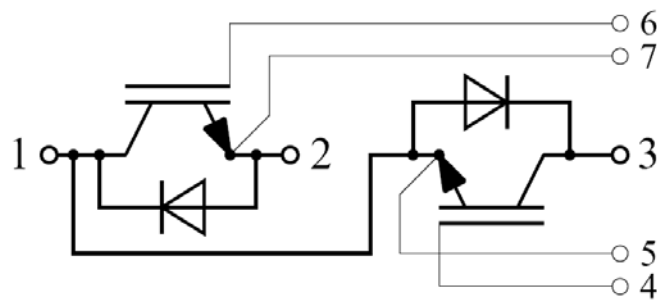
Fig 9. Diode Switching Loss vs. R_G 

Fig 10. Diode Transient Thermal Impedance

Circuit Schematic**Package Dimensions**

Dimensions in Millimeters

